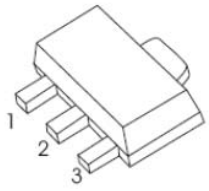
SOT-89-3L Plastic-Encapsulate Transistors

KTC3205 TRANSISTOR (NPN)

SOT-89-3L



1. BASE
2. COLLECTOR
3. EMITTER

FEATURES

- High current application
- Complementary to KTA1273

MAXIMUM RATINGS(T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2	A
P_C	Collector Dissipation	0.5	W
T_J, T_{stg}	Junction and Storage Temperature	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 1mA , I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 10mA, I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}= 30V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}= 2 V, I_C= 500 mA	100		320	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C= 1.5A, I_B= 30 mA			2.0	V
Base-emitter voltage	V_{BE}	V_{CE}=2V, I_C= 500mA			1.0	V
Transition frequency	f_T	V_{CE}=2V, I_C= 500mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0V,f=1MH$_Z$		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320